SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

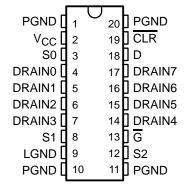
- Low r_{DS(on)} . . . 1.3 Ω Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Four Distinct Function Modes
- Low Power Consumption

description

This power logic 8-bit addressable latch controls open-drain DMOS transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multifunctional device capable of storing single-line data in eight addressable latches with 3-to-8 decoding or demultiplexing mode active-low DMOS outputs.

Four distinct modes of operation are selectable by controlling the clear (\overline{CLR}) and enable (\overline{G}) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable \overline{G} should be held high (inactive) while the address lines are changing. In the 3-to-8 decoding

DW OR N PACKAGE (TOP VIEW)



FUNCTION TABLE

INI	PUT	S	OUTPUT OF	EACH	FUNCTION
CLR	G	D	ADDRESSED DRAIN	OTHER DRAIN	FUNCTION
H H	L L	H L	L H	Q _{io} Q _{io}	Addressable Latch
Н	Н	Х	Q _{io}	Q _{io}	Memory
L L	L L	H L	L H	H H	8-Line Demultiplexer
L	Н	Х	Н	Н	Clear

LATCH SELECTION TABLE

SELE	CT IN	DRAIN	
S2	S1	S0	ADDRESSED
L	L	L	0
L	L	Н	1
L	Н	L	2
L	Н	Н	3
Н	L	L	4
Н	L	Н	5
Н	Н	L	6
Н	Н	Н	7

or demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 9, logic ground (LGND), and pins 1, 10, 11, and 20, power ground (PGND) must be externally made in a manner that reduces crosstalk between the logic and load circuits.

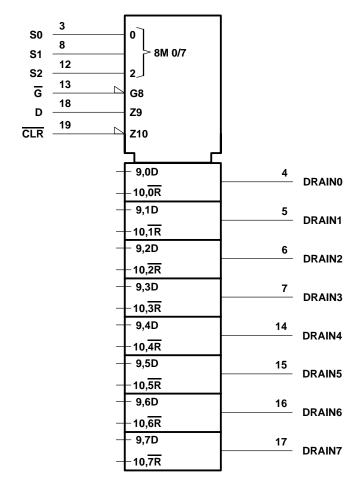
The TPIC6259 is characterized for operation over the operating case temperature range of -40° C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

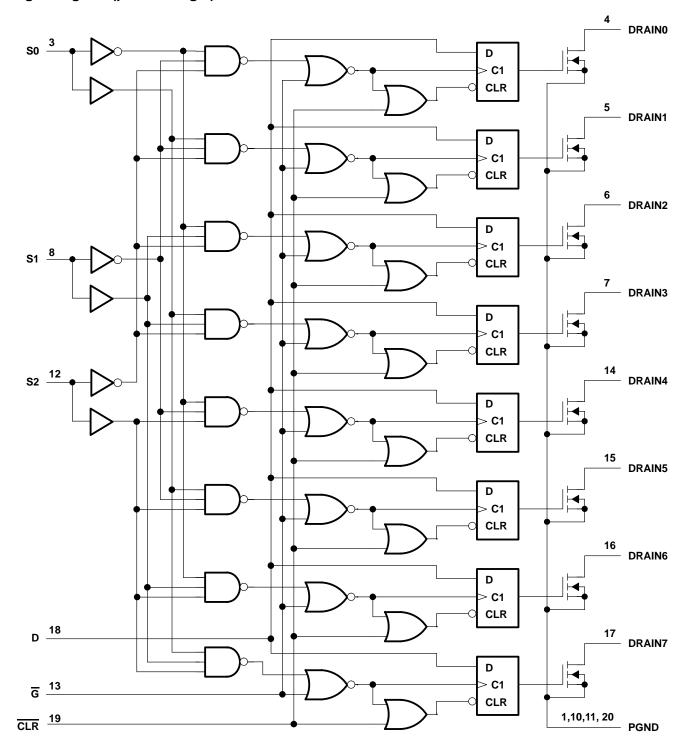


logic symbol†



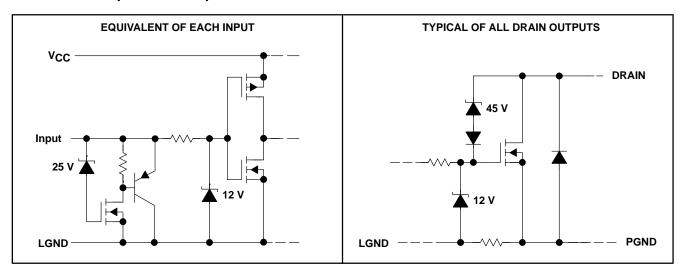
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

schematic of inputs and outputs



absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted)†

Logic supply voltage, V _{CC} (see Note 1)	
Logic input voltage range, V _I	
Power DMOS drain-to-source voltage, V _{DS} (see Note 2)	45 V
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current	2 A
Pulsed drain current, each output, all outputs on, I_{Dn} , $T_A = 25^{\circ}C$ (see Note 3)	750 mA
Continuous drain current, each output, all outputs on, I_{Dn} , $T_A = 25$ °C	250 mA
Peak drain current single output, I _{DM} , T _A = 25°C (see Note 3)	
Single-pulse avalanche energy, E _{AS} (see Note 4)	
Avalanche current, I _{AS} (see Note 4)	
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T _J	–40°C to 150°C
Storage temperature range, T _{stg}	
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to LGND and PGND.
 - 2. Each power DMOS source is internally connected to PGND.
 - 3. Pulse duration \leq 100 µs, duty cycle \leq 2%
 - 4. DRAIN supply voltage = 15 V, starting junction temperature, (TJS) = 25°C, L = 100 mH, IAS = 1 A (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \leq 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 125°C POWER RATING
DW	1125 mW	9.0 mW/°C	225 mW
N	1150 mW	9.2 mW/°C	230 mW



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

recommended operating conditions over recommended operating temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Logic supply voltage, V _{CC}	4.5	5.5	V
High-level input voltage, V _{IH}	0.85 V _{CC}		V
Low-level input voltage, V _{IL}		0.15 V _{CC}	V
Pulsed drain output current, T _C = 25°C, V _{CC} = 5 V (see Notes 3 and 5)	-1.8	1.5	Α
Setup time, D high before $\overline{G} \uparrow$, t _{SU} (see Figure 2)	10		ns
Hold time, D high after \overline{G} ↑, t _h (see Figure 2)	5		ns
Pulse duration, t _W (see Figure 2)	15		ns
Operating case temperature, T _C	-40	125	°C

electrical characteristics, V_{CC} = 5 V, T_{C} = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDITI	ONS	MIN	TYP	MAX	UNIT
V _{(BR)DSX}	Drain-source breakdown voltage	I _D = 1 mA			45			V
V_{SD}	Source-drain diode forward voltage	$I_F = 250 \text{ mA},$	See Note 3			0.85	1	V
lιΗ	High-level input current	$V_{CC} = 5.5 \text{ V},$	$V_I = V_{CC}$				1	μΑ
I _I L	Low-level input current	$V_{CC} = 5.5 \text{ V},$	V _I = 0				-1	μΑ
ICC	Logic supply current	I _O = 0,	All inputs low			15	100	μΑ
IN	Nominal current	V _{DS(on)} = 0.5 V _s See Notes 5, 6, a	$I_N = I_D$, and 7	T _C = 85°C,		250		mA
lnov	Off-state drain current	V _{DS} = 40 V				0.05	1	
IDSX	On-state drain current	V _{DS} = 40 V,	T _C = 125°C			0.15	5	μΑ
		I _D = 250 mA,	V _{CC} = 4.5 V			1.3	2	
rDS(on)	Static drain-source on-state resistance	I _D = 250 mA, V _{CC} = 4.5 V	T _C = 125°C,	See Notes 5 and 6 and Figures 8 and 9		2	3.2	Ω
		I _D = 500 mA,	V _{CC} = 4.5 V]		1.3	2	

switching characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output from D	625				ns
tPHL	Propagation delay time, high-to-low-level output from D	$C_{\rm I} = 30 \rm pF, \qquad I_{\rm D} = 250 \rm mA, \qquad 140$			ns	
t _r	Rise time, drain output	See Figures 1, 2, and 10		650		ns
t _f	Fall time, drain output			400		ns
ta	Reverse-recovery-current rise time	I _F = 250 mA, di/dt = 20 A/μs,		100		
t _{rr}	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		ns

NOTES: 3. Pulse duration $\leq 100 \,\mu\text{s}$, duty cycle $\leq 2\%$

- 5. Technique should limit $T_J T_C$ to 10°C maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- 7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_C = 85°C.

thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT	
D	9JA Thermal resistance junction-to-ambient	DW package	All Q autoute with equal power		111	°C AM
$R_{\theta JA}$		N package	All 8 outputs with equal power		108	°C/W



PARAMETER MEASUREMENT INFORMATION

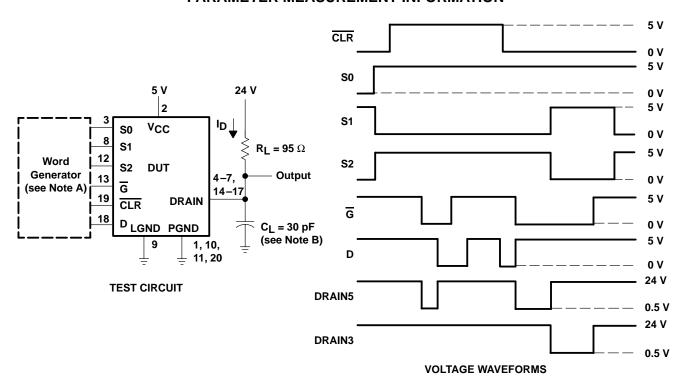


Figure 1. Typical Operation Mode

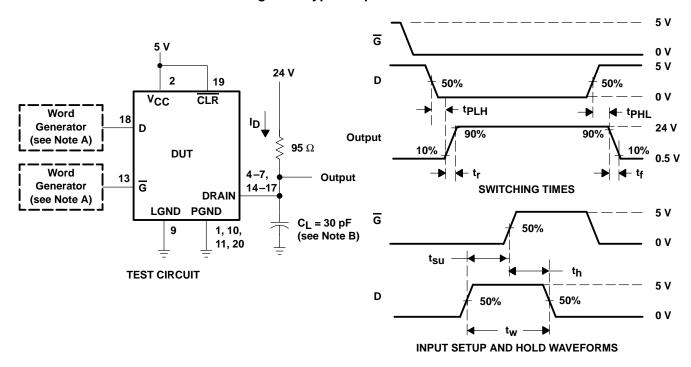


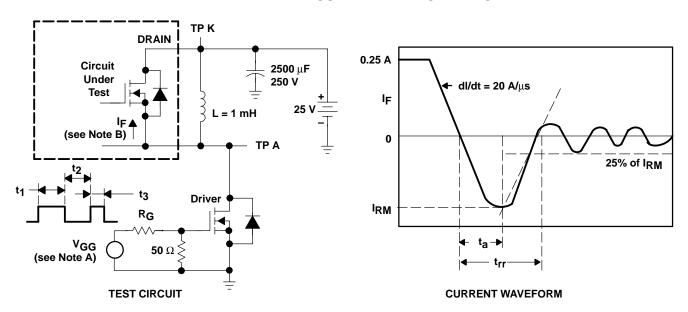
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

NOTES: A. The word generator has the following characteristics: $t_{\Gamma} \le 10$ ns, $t_{W} = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_{O} = 50 \ \Omega$.

B. C_L includes probe and jig capacitance.

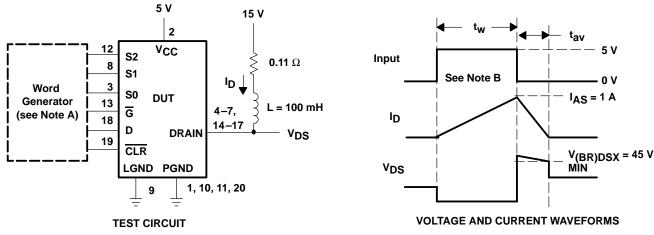


PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The VGG amplitude and RG are adjusted for di/dt = 20 A/ μ s. A VGG double-pulse train is used to set IF = 0.25 A, where t_1 = 10 μ s, t_2 = 7 μ s, and t_3 = 3 μ s.
 - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

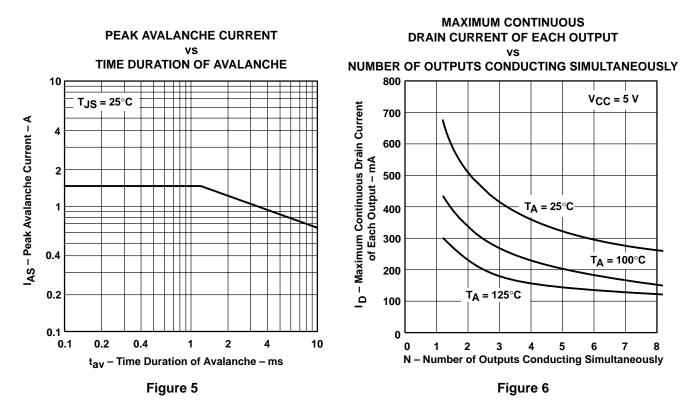
Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



- NOTES: A. The pulse generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $z_0 = 50 \ \Omega$.
 - B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 1$ A. Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 75$ mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS



MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT vs

NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

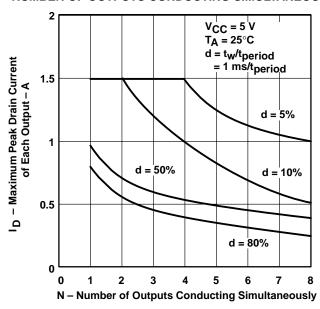
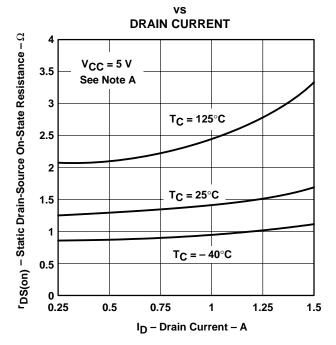


Figure 7

TYPICAL CHARACTERISTICS

STATIC DRAIN-SOURCE ON-STATE RESISTANCE



STATIC DRAIN-SOURCE ON-STATE RESISTANCE

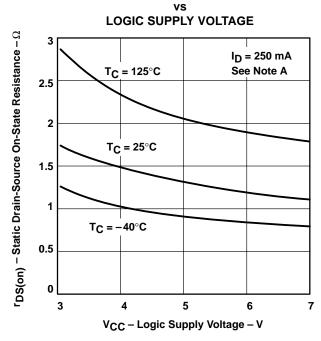


Figure 8 Figure 9

SWITCHING TIME

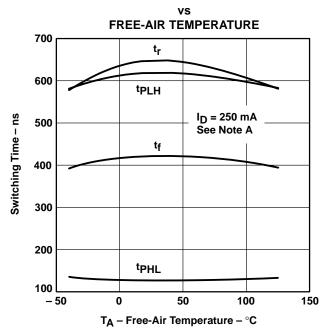


Figure 10

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.



www.ti.com 11-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TPIC6259DW	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259
TPIC6259DW.A	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259
TPIC6259DWG4	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-	TPIC6259
TPIC6259DWG4.A	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259
TPIC6259DWR	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259
TPIC6259DWR.A	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259
TPIC6259DWRG4	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-	TPIC6259
TPIC6259DWRG4.A	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6259
TPIC6259N	Active	Production	PDIP (N) 20	20 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TPIC6259N
TPIC6259N.A	Active	Production	PDIP (N) 20	20 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TPIC6259N

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

www.ti.com 11-Nov-2025

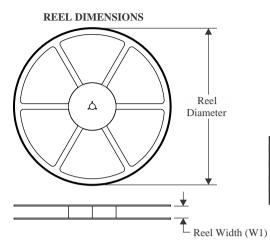
and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

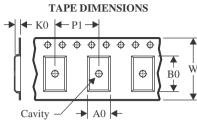
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 23-May-2025

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

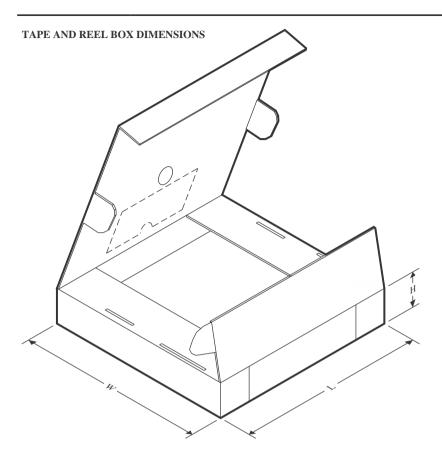
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6259DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
TPIC6259DWRG4	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

www.ti.com 23-May-2025



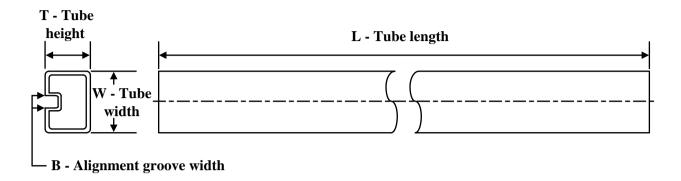
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6259DWR	SOIC	DW	20	2000	350.0	350.0	43.0
TPIC6259DWRG4	SOIC	DW	20	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

www.ti.com 23-May-2025

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPIC6259DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
TPIC6259DW.A	DW	SOIC	20	25	506.98	12.7	4826	6.6
TPIC6259DWG4	DW	SOIC	20	25	506.98	12.7	4826	6.6
TPIC6259DWG4.A	DW	SOIC	20	25	506.98	12.7	4826	6.6
TPIC6259N	N	PDIP	20	20	506	13.97	11230	4.32
TPIC6259N.A	N	PDIP	20	20	506	13.97	11230	4.32

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025